



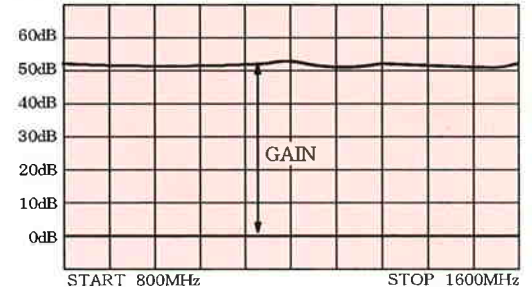
# MICROWAVE GaAs FET AMPLIFIER

## MODEL R&K A2000L-100-R

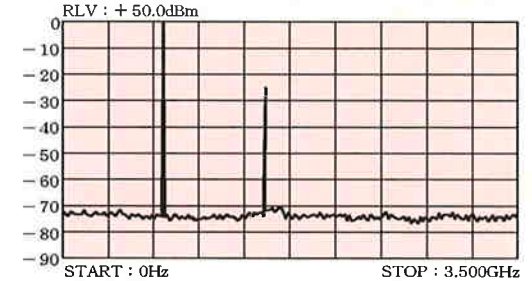
- BROADBAND FREQUENCY : 800~1600MHz
- HIGH POWER : **100W min.** (@1dB Comp.)
- HIGH RELIABILITY GaAs FET CONSTRUCTION
- AM · FM · SSB CW · PULSE
- 19 INCHES RACK SIZE



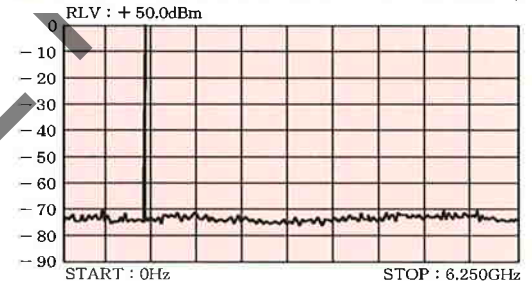
### ■ SMALL SIGNAL GAIN



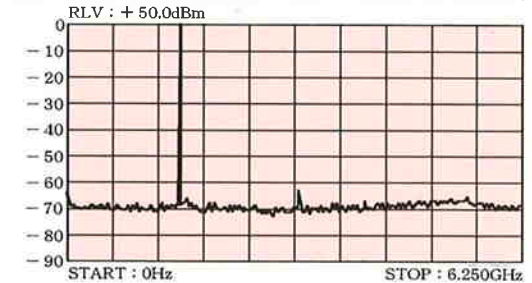
### ■ HARMONICS (Fo = 0.8GHz/100W)



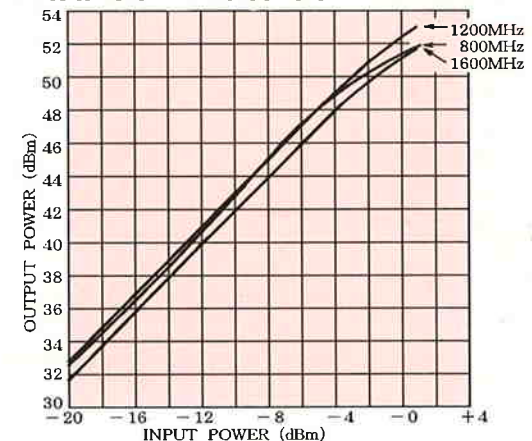
### ■ HARMONICS (Fo = 1.2GHz/100W)



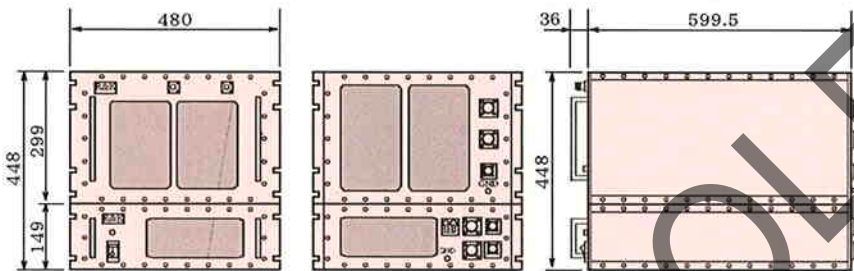
### ■ HARMONICS (Fo = 1.6GHz/100W)



### ■ INPUT-OUTPUT LINEARITY



### DIMENSIONS



### SPECIFICATIONS

1. Input/Output Frequency Range 800MHz~1600MHz (min.)
2. Small Signal Gain +50dB (min.)
3. Power Gain @1dB Compression +49dB (min.)
4. Power Gain Flatness ±2.0dB (max.)
5. Power Output (@1dB Comp.) 100W (min.)
6. Amplifier Operation Mode Class A Linear
7. 2 Tone 3rd Order Intercept Point +60dBm (typ.)
8. Input/Output Impedance 50 Ω Nominal
9. Input VSWR 2.0 (max.)
10. Output VSWR 1.5 (max.)
11. Harmonics -18dBc (max.) @ Full Power
12. Spurious -60dBc (max.) @ Full Power
13. Input Noise Figure 10dB (typ.)
14. Output Power Duty Ratio 100% C.W.
15. Connectors RF Input N - Female  
RF Output N - Female
16. AC Supply Input Connector Cannon Type AC Connector
17. Ground Connector Terminal On Back Panel  
Integral AC/Ground Connector  
Protected Infinite VSWR (with Circulator)  
+65°C Internally Protected  
30.0A (max)  
200V, AC·50/60Hz·15A(max.)
22. Cooling Integral Forced Air Cooling
23. Operating Temperature -10°C~+45°C
24. Storage Temperature -15°C~+65°C
25. Weight 60.0kg



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